



Retraction

RETRACTED: Kang et al. Achievement of Gradual Conductance Characteristics Based on Interfacial Phase-Change Memory for Artificial Synapse Applications. *Electronics* 2020, 9, 1268

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The authors and journal retract the article, “Achievement of Gradual Conductance Characteristics Based on Interfacial Phase-Change Memory for Artificial Synapse Applications” [1], cited above.

Following its publication, the authors contacted the editorial office about incorrect use of materials and data used without authorization (as shown in Figure 1, the TEM images, and XRD data used).



Citation: Kang, S.; Lee, J.; Kang, M.; Song, Y. RETRACTED: Kang et al. Achievement of Gradual Conductance Characteristics Based on Interfacial Phase-Change Memory for Artificial Synapse Applications. *Electronics* 2020, 9, 1268. *Electronics* 2021, 10, 408. <https://doi.org/10.3390/electronics10040408>

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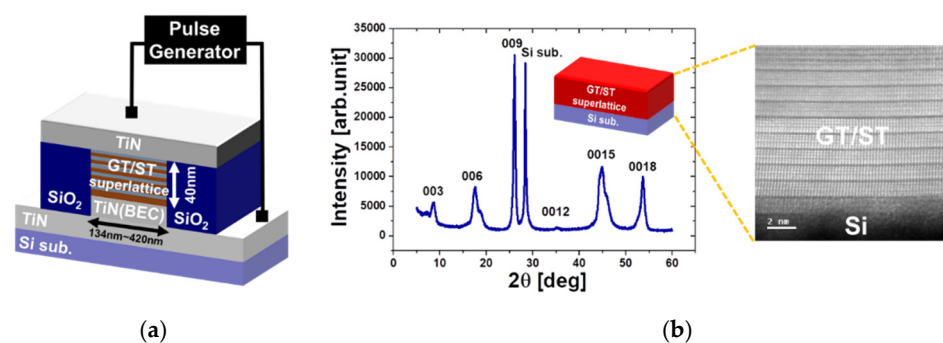


Figure 1. (a) Schematic of the fabricated GeTe/Sb₂Te₃ (GT/ST) interfacial phase-change memory (iPCM) structure, (b) XRD diffraction pattern of a GT/ST SL (SL) structure and cross-sectional TEM image of the GT/ST superlattice on an Si (111) substrate.

The article [1] describes the use of a superlattice device based on the GeTe/Sb₂Te₃ material (Figure 1b). The device actually measured Ti-doped material, not GeTe/Sb₂Te₃ material. Further details were provided by the university that confirmed the extent of the issues described.

This retraction was approved by the Editor-in-Chief of the journal *Electronics*. The authors would like to apologize for any inconvenience caused to the readers by these changes.

Reference

1. Kang, S.; Lee, J.; Kang, M.; Song, Y. RETRACTED: Achievement of Gradual Conductance Characteristics Based on Interfacial Phase-Change Memory for Artificial Synapse Applications. *Electronics* 2020, 9, 1268. [\[CrossRef\]](#)